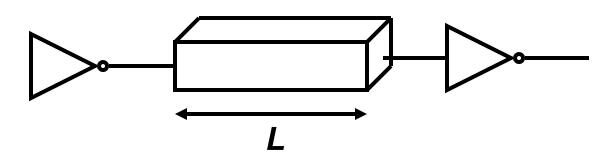
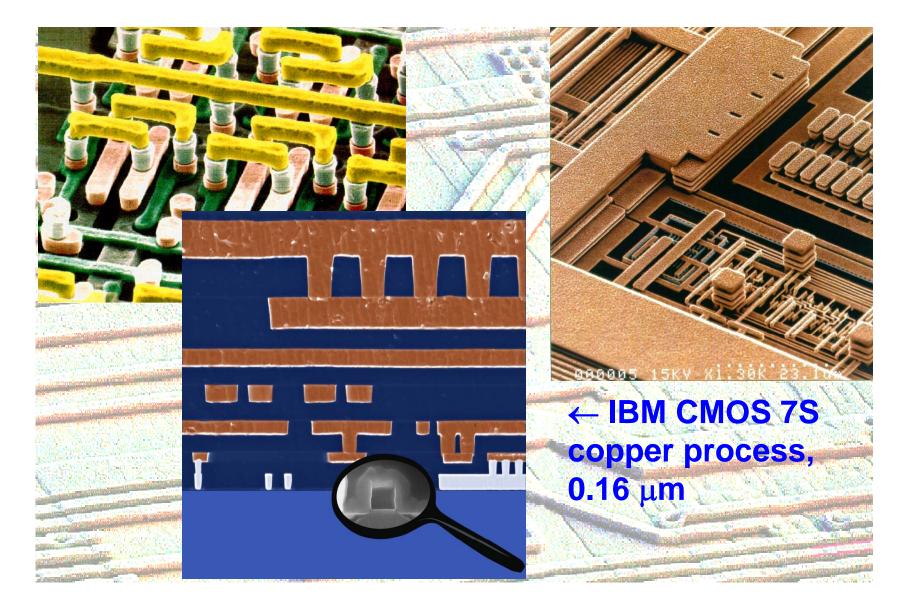


Interconnect



- Wires are not ideal interconnections
- They may have non-negligible capacitance, resistance, inductance
- These are called wire parasitics
- Can dominate performance of chip
- Must be accounted for during design
- Using approximate models
- Detailed post-layout verification also necessary

Wires



Interconnect Hierarchy

	M6	
	M5	Global
	M4	intermodule
	M3	
substrate	M2 M1 poly	Intercell Intracell

Cross-section of IBM 0.13 μ process

Example Interconnect Hierarchy for typical 0.25µ process (Layer Stack)

Outline

Capacitance

Area/perimeter model, coupling

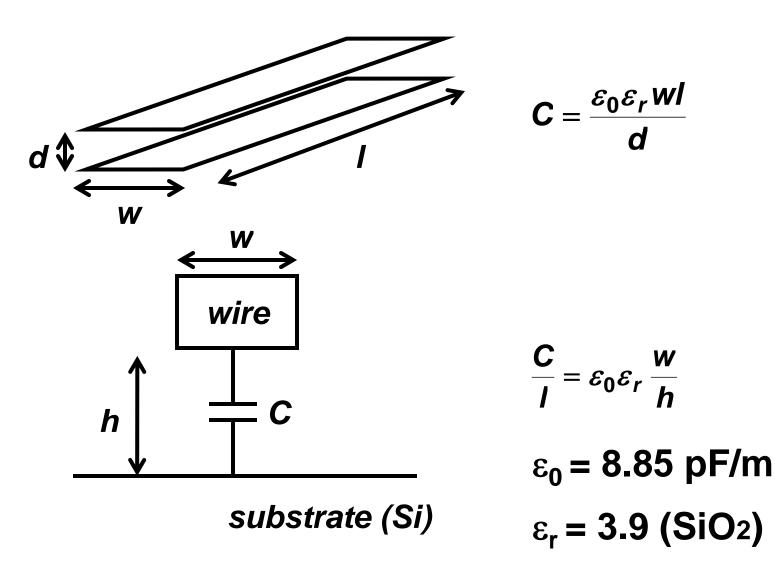
Resistance

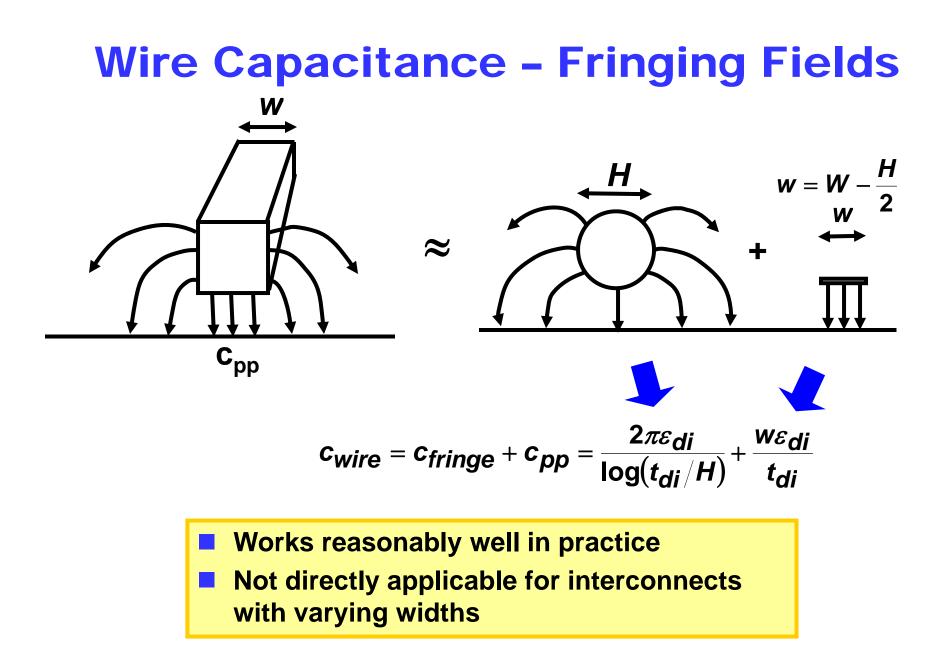
- **Sheet resistance**
- Interconnect delay
 - Delay metrics, rc delay, Elmore delay

Capacitance

Area/perimeter model, coupling

Wire Capacitance - Parallel Plate





Wire Capacitance -Area/Perimeter Model

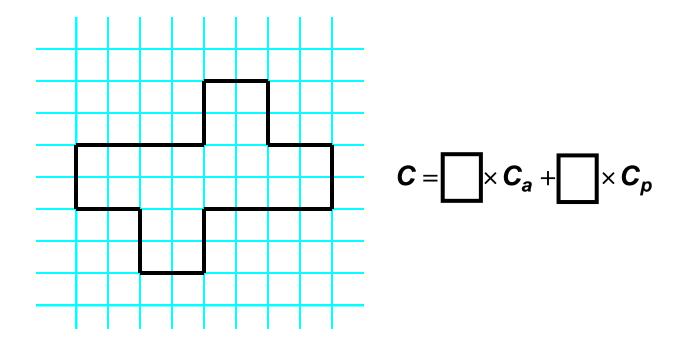
- Ca was calculated with modified wire width
- Formula inapplicable for irregular interconnects (nonconstant width)



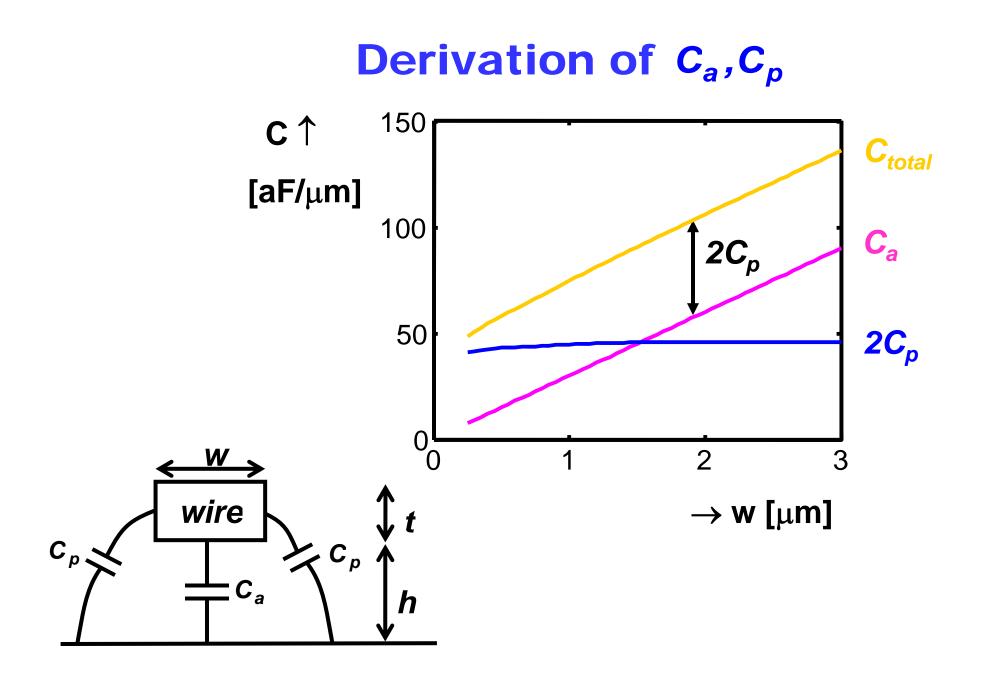
More practical approximation

$\boldsymbol{C} = \boldsymbol{A} \times \boldsymbol{C}_{\boldsymbol{a}} + \boldsymbol{P} \times \boldsymbol{C}_{\boldsymbol{p}}$	units	alternative
A = Area	m ²	μm^2
C _a = Area capacitance	F / m ²	$aF/\mu m^2$
P = Perimeter	т	μ m
$C_{p} = Perimeter capacitance$	F/m	aF / μm
1μ \downarrow \longrightarrow 10μ	$\mathbf{C} = \mathbf{\Box} \times \mathbf{C}$	a +

Area / Perimeter Capacitance Model



Question: How to derive C_a, C_p ? How accurate is this model?



Derivation of C_a, C_p

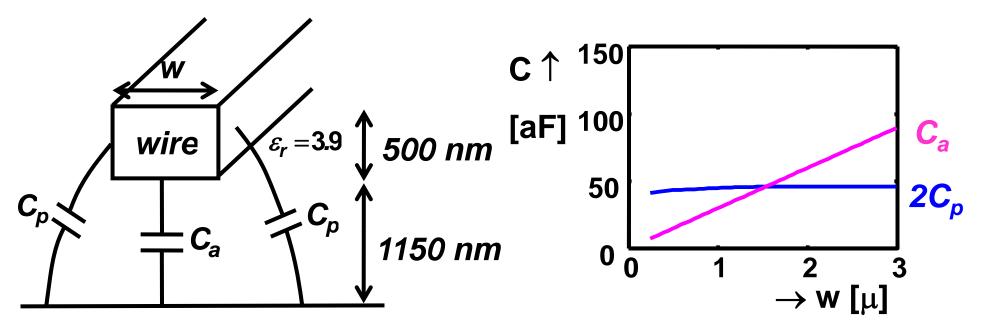
- 2D (cross-section) numerical computation (or measurement)
- $\Box C_1$: total wire capacitance per unit length

$$\mathbf{C}_a = \varepsilon_0 \varepsilon_r / h$$

$$\mathbf{C}_{p} = \mathbf{1}/\mathbf{2}(\mathbf{C}_{I} - \mathbf{C}_{a} \times \mathbf{W})$$

- C_p depends on t, h → determined by technology, layer
- C_p would depend slightly on w (see previous graph), this dependence is often ignored in practice

Area / Perimeter Capacitance

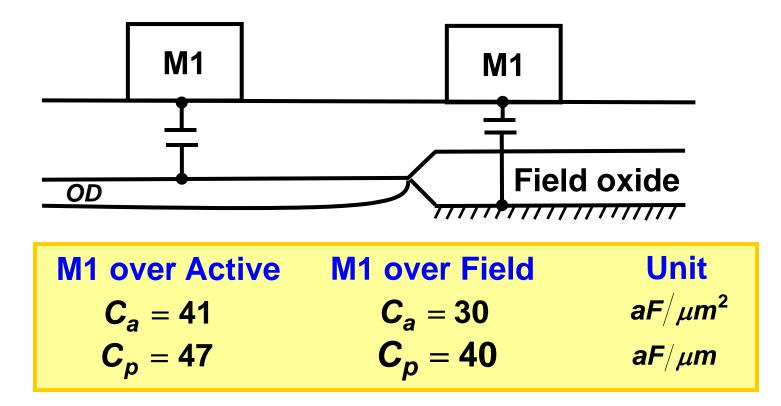


C $_{p}$ dominates for many wires

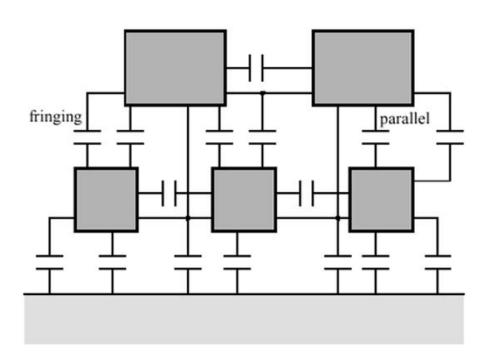
- **C** $_{p}$ may not be neglected
- A constant value for C_{p} is usually a good approximation
- C_{p} is sometimes called C_{f} (fringe capacitance)

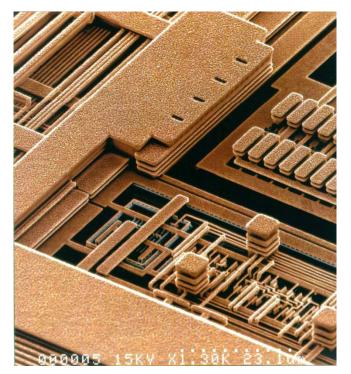
Interconnect Capacitance Design data

- See Table 4.2 (or inside backside cover)
- Example: M1 over Field vs. M1 over Active (hypothetical)

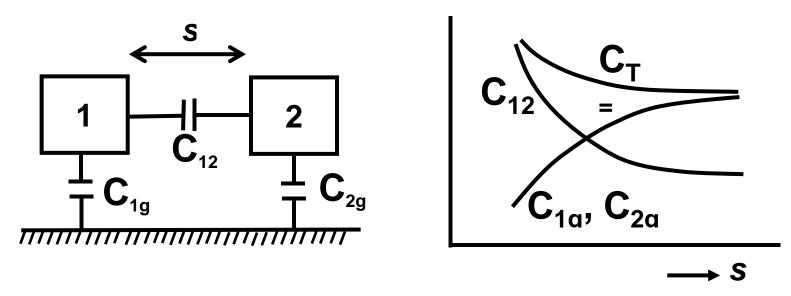


Coupling Capacitances





Coupling Capacitances (2)



•
$$C_T = C_{1g} + C_{12} = C_{2g} + C_{12}$$
 fairly constant

- Use that as first order model
- Interconnect capacitance design data (e.g. Table 4.3)

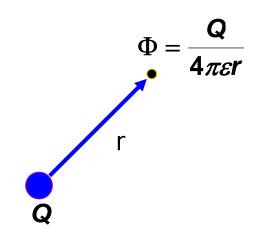
Field Solvers

- Numerical, physics based technique for accurately computing capacitances
- Based on 3D geometry
- Finite element method
- Finite difference method

Boundary element method

Solve huge sets of equations, fast

BEM for Capacitance Computation



 $\Phi(p) = \int G(p,q)\xi(q)dq$ all charge

Electrostatic potential due to point charge

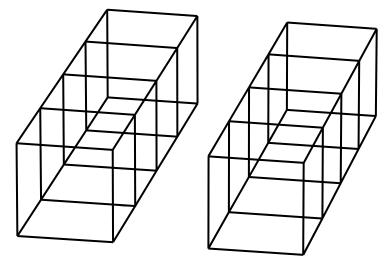
Electrostatic potential due to charge distribution

Green's function G(p,q):

potential at a point in space (x_p, y_p, z_p) due to unit point charge at other point (x_q, y_q, z_q) .

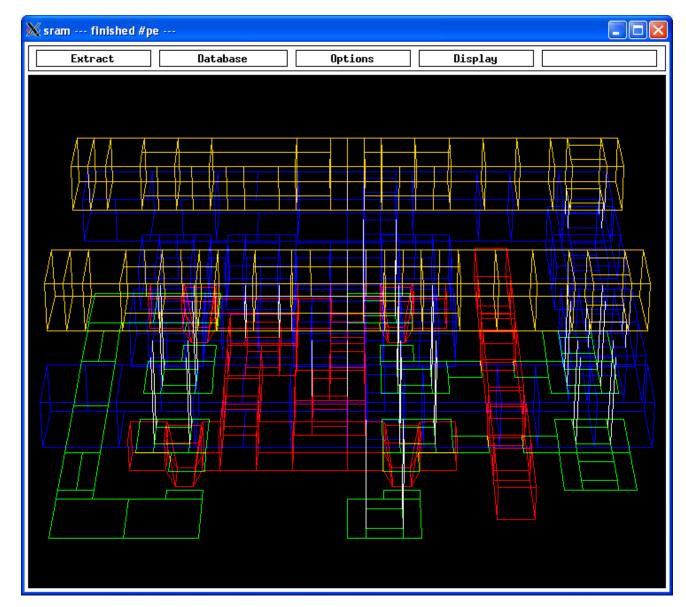
Boundary Element Method, Discretization

$\mathbf{Q} = \mathbf{F}^{T} \mathbf{G}^{-1} \mathbf{F} \Phi$	
C _S = F ^T G ⁻¹ F	



- Q: vector of conductor charges
- Φ: vector of conductor potentials
- Q: vector of panel (discretization element) charges
- φ: vector of panel potentials
- F: incidence matrix relating panels to conductors
 (Q = F^Tq and φ = FΦ)
- G_{ij}: potential of panel i due to charge at panel j
- C_s short-circuit capacitance matrix to be obtained

Demo

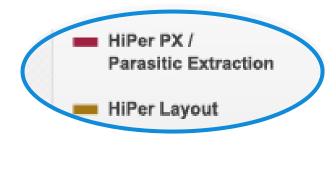


SPACE - OEM

- SPACE aka OptEM Inspector aka Tanner HiPer PX
- 2009 was slow

TUDelft

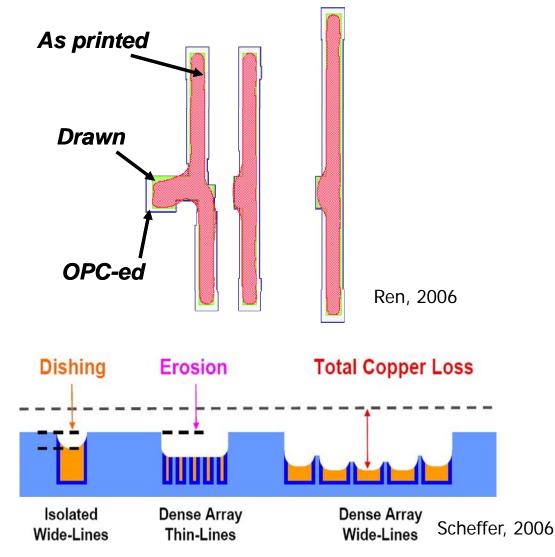
- Recently signs of more (eval) activity
- Sales can still be easily counted

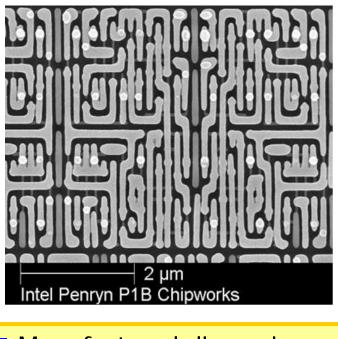




21

Manufacturing Variability – Field Solving needs Next Level....

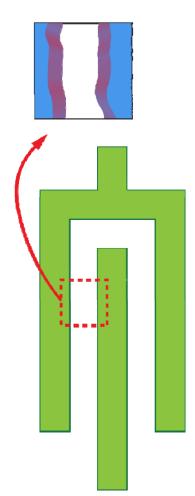




- Manufactured dimensions ≠ drawn dimensions
- Both systematic and stochastic variations
- Need for inclusion in verification flow

Interconnect Modeling with Variability

- Systematic variations e.g. litho induced
- Stochastic variations e.g. line edge roughness
- Systematic aspects of resistance variability
- Stochastic variations of capacitance
- Measurement/validation campaign with/at Holst Centre
- Joint statistical modeling flow together with INESC-ID (affiliated to TU Lisbon) for Parametric Model Order Reduction

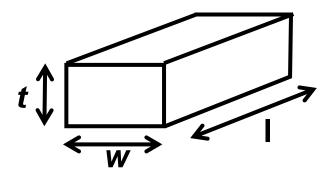




Resistance

Sheet resistance

Wire Resistance



- Proportional to I
- Inversely proportional to w and t (cross-sectional area)
- Proportional to ρ: specific resistance, material property [Ωm]
- R = ρl/wt
- Aluminum: ρ = 2.7x10⁻⁸ Ωm

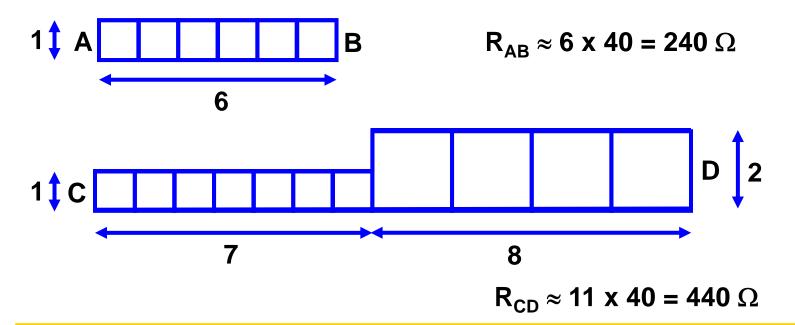
Copper: $\rho = 1.7 \times 10^{-8} \Omega m$

Sheet Resistance

- R = ρl/wt
- **t**, ρ constant for layer, technology
- R = RI/w
- R : sheet resistance [Ω/] resistance of a square piece of interconnect other symbol: R_s
- Interconnect resistance design data e.g. Table 4.5 (or inside back-cover)

Interconnect Resistance

- Assume $R_{\Box} = 40 \Omega$
- Estimate the resistance between A and B in the wire below.



Engineering is about making controlled approximations to something that is too complicated to compute exactly, while ensuring that the approximate answer still leads to a working (functional, safe, ...) system

Exercise

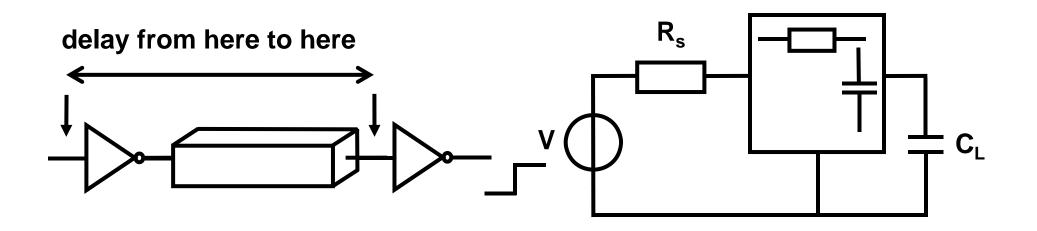
An interconnect line is made from a material that has a resistivity of $\rho = 4 \ \mu\Omega$ -cm. The interconnect is 1200 Å thick, where 1 Angstrom (Å) is 10⁻¹⁰ m. The line has a width of 0.6 μ m.

- a) Calculate the sheet resistance R_{\Box} of the line.
- b) Find the line resistance for a line that is 125 μ m long.

Interconnect delay

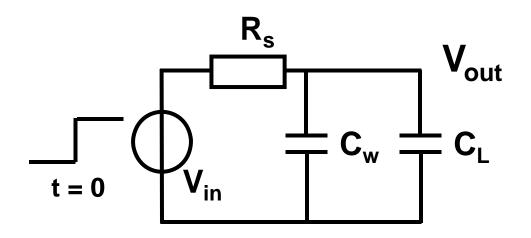
Delay metrics, rc delay, Elmore delay

Delay



- Model driver as linearized Thevenin source V, R_s, assume step input
- Model load as C_L
- Wire is an RC network (two-port)

Wire Capacitance



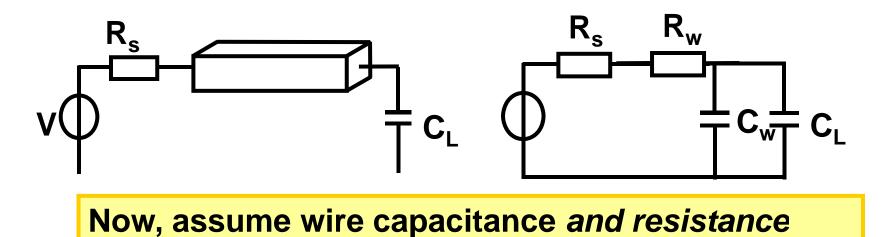
Assume wire behaves purely capacitive

$$(C_w + C_L)\frac{dV_{out}}{dt} + \frac{V_{out} - V_{in}}{R_s} = 0$$

$$V_{out} = V_{in} - \tau \frac{dV_{out}}{dt}$$
 $\tau = R_s (C_w + C_L)$

$$V_{out} = (1 - e^{-t/\tau}) V_{in}$$

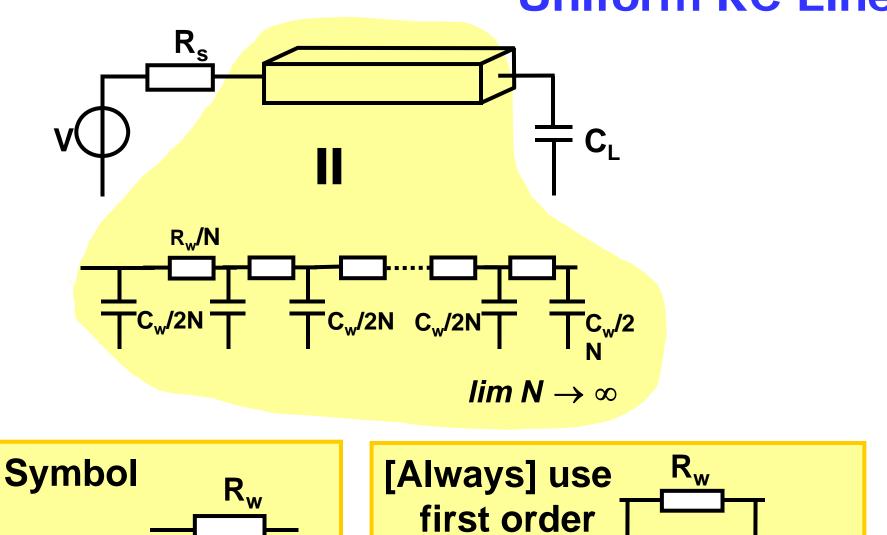
Wire Resistance



$$\tau = (\boldsymbol{R}_{s} + \boldsymbol{R}_{w})(\boldsymbol{C}_{w} + \boldsymbol{C}_{L})$$

Not a a good model

R and C are distributed along the wire



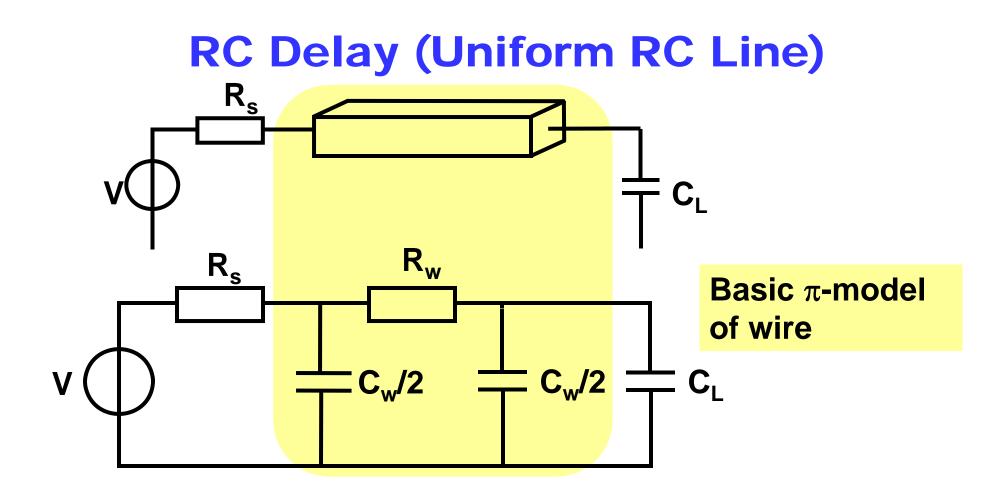
model

Uniform RC Line

TUD/EE ET4293 -digic - 1213 - © NvdM - interconnect

C_w/2

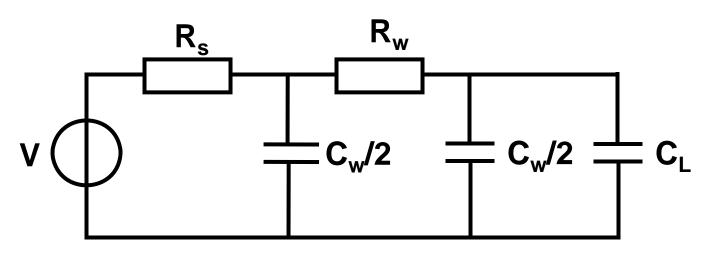
C_w/2



Not 1 τ

Elmore delay: equivalent effective *τ*

Equivalent Time Constant



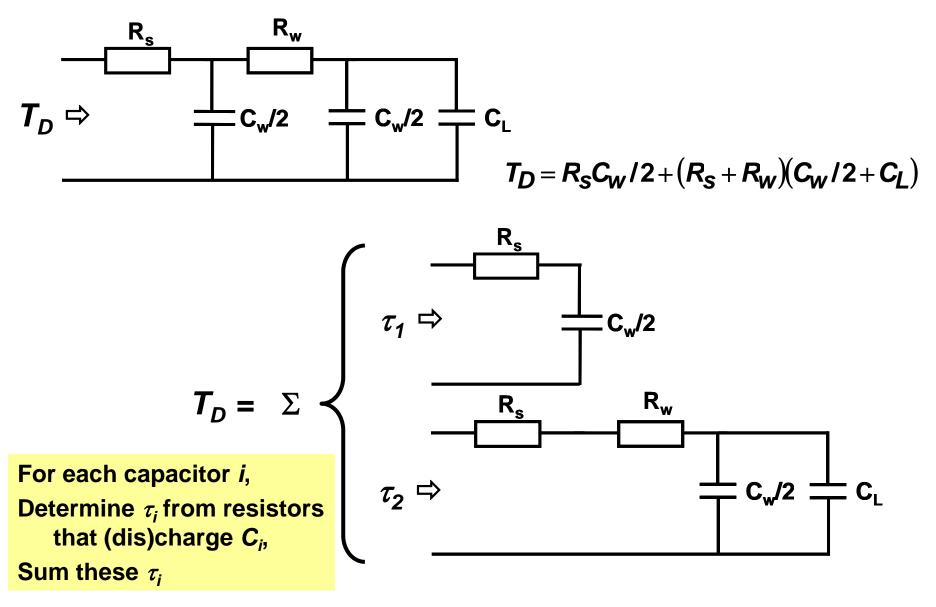
- Multiple time-constants
- Need for one "equivalent" number
- Offered by Elmore Delay T_D

$$T_D = R_s C_w / 2 + (R_s + R_w)(C_w / 2 + C_L)$$

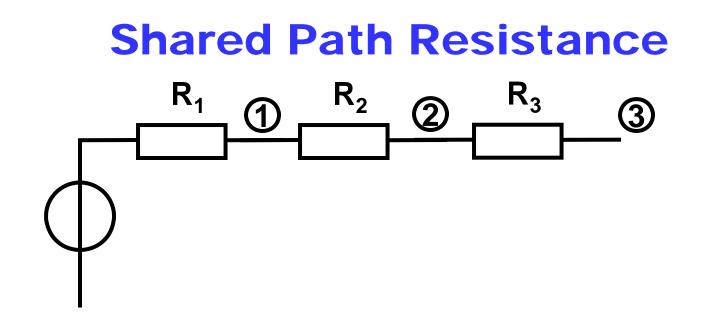
How to compute Elmore Delay?

Effective "one number" model for delay

Equivalent Time Constant

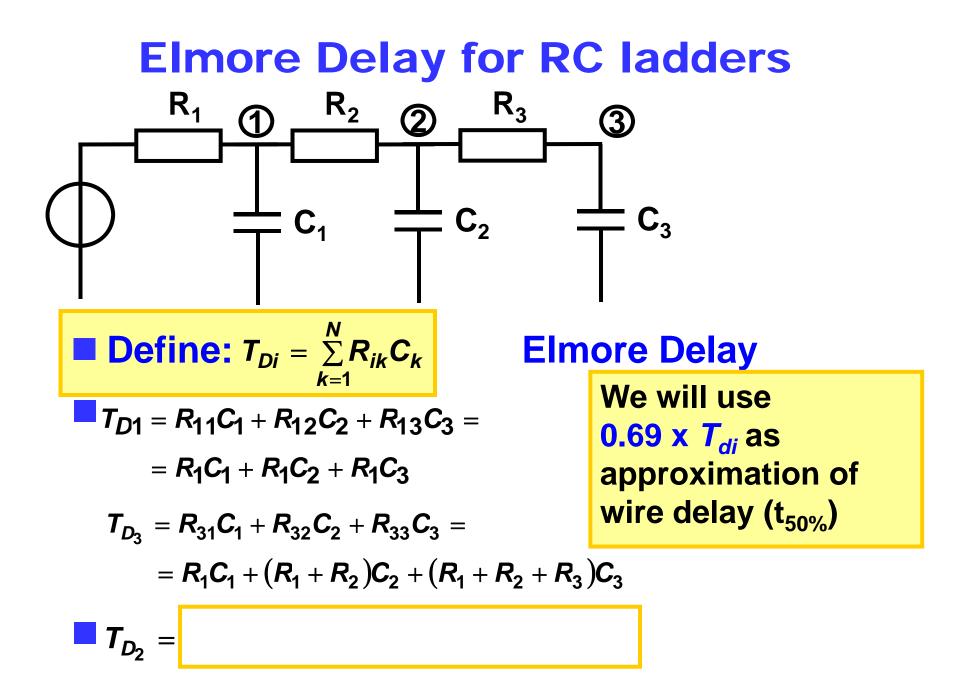


TUD/EE ET4293 -digic - 1213 - © NvdM - interconnect

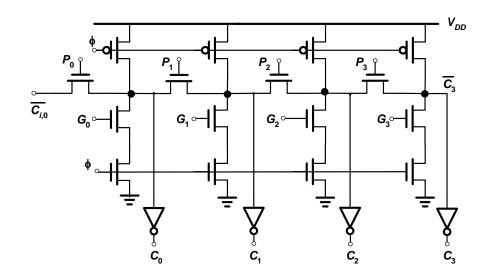


- Define: R_{ii} = Resistance from node i to input
- Example: $R_{11} = R_1$ $R_{22} = R_1 + R_2$ $R_{33} = R_1 + R_2 + R_3$
- Define: R_{ik} = Shared path resistance to input for node i and k

$$R_{12} = R_1 R_{13} = R_1 R_{23} =$$

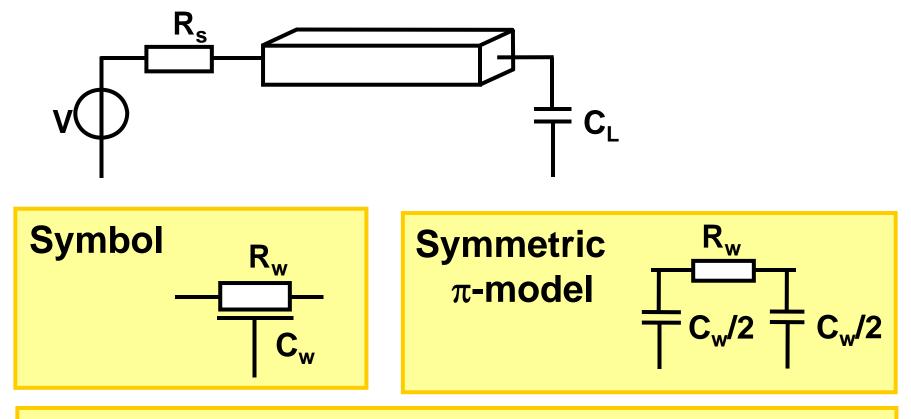


Manchester Carry Chain Delay



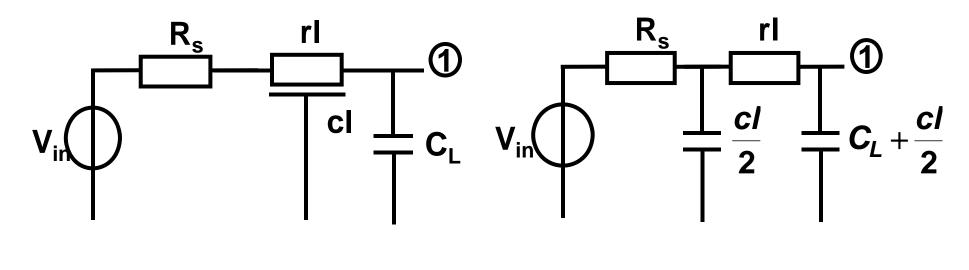
Given an expression of delay (symbols, not numbers) as a function of the number of bits

Elmore Delay for Distributed RC Lines



Theorem: For Elmore Delay calculations, each uniform distributed RC section is equivalent to a symmetric π-model

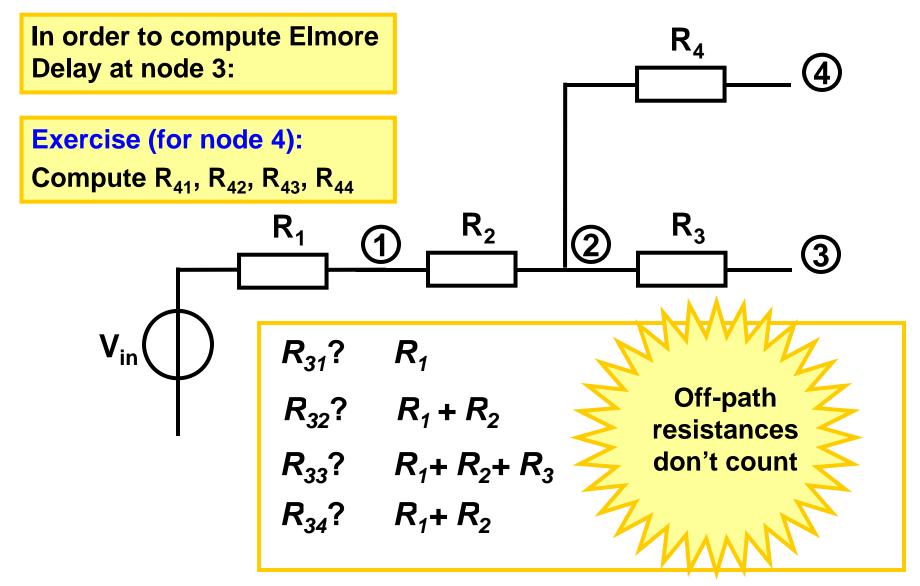
Canonical Driver-Line-Load



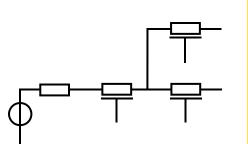
$$T_{D_1} = R_s \frac{cl}{2} + (R_s + rl) \left(C_L + \frac{cl}{2} \right)$$
$$= R_s (cl + C_L) + rlC_L + \frac{1}{2} rcl^2$$

Delay quadratic in line length

Shared Path Resistance for Tree Structures

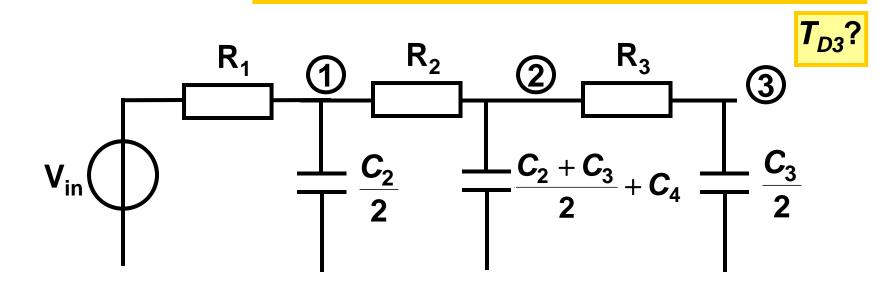


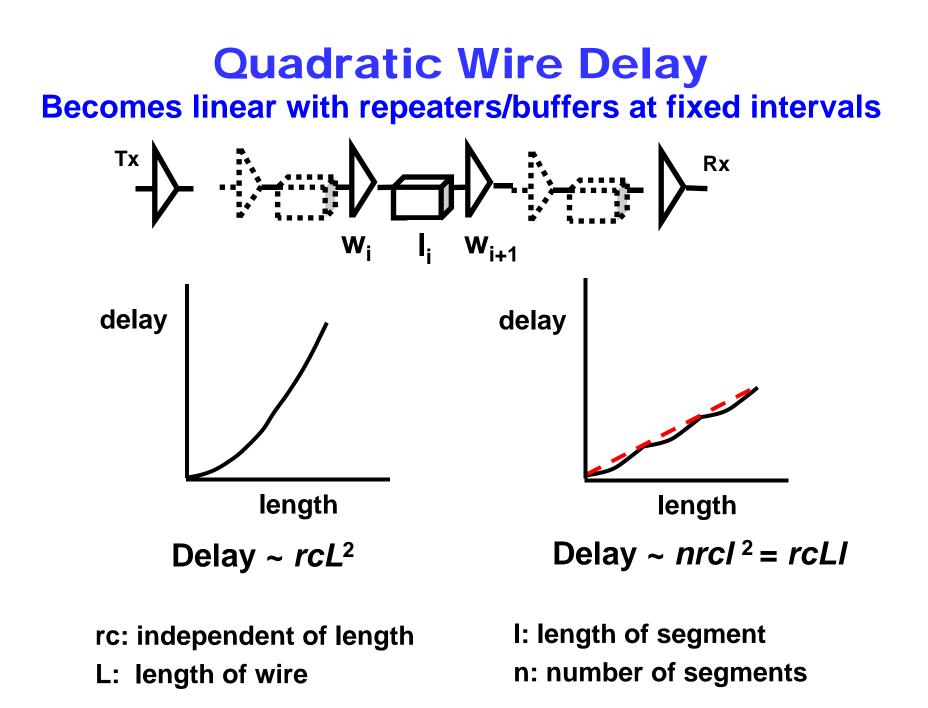
Elmore Delay for Tree Structures



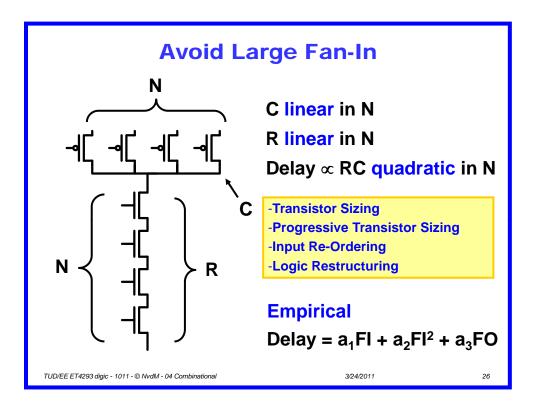
Exercise: Compute T_{D1}, T_{D2}, T_{D3}, T_{D4}

- **Replace RC lines by** π -sections
- Given observation node i, then only resistances along the path from input to node i can possibly count
- Make others zero
- Compute as if RC ladder

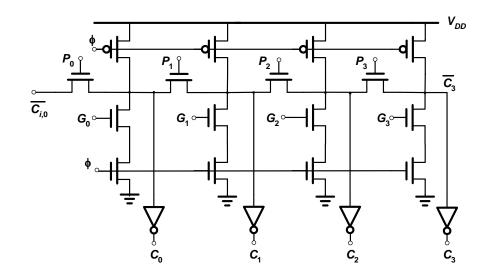




Quadratic RC Delay Issues also in Logic



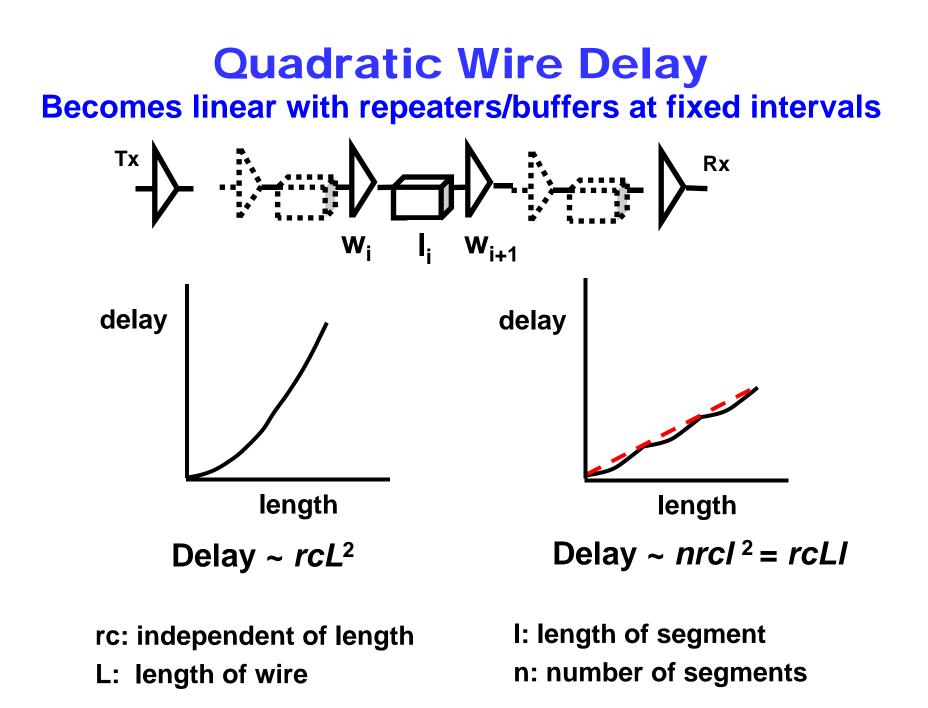
Manchester Carry Chain Delay



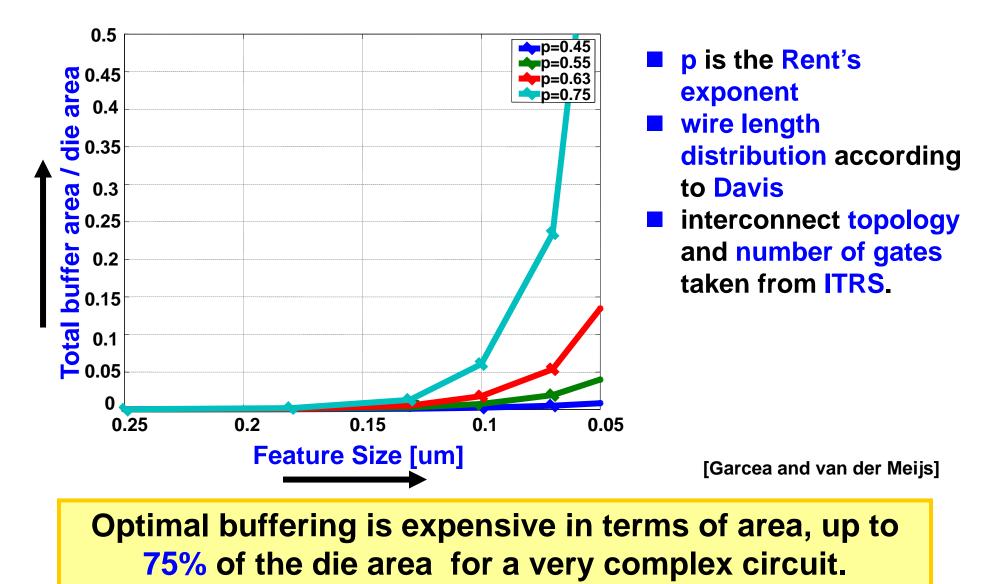
Given an expression of delay (symbols, not numbers) as a function of the number of bits -> O(N²)

How to break this relationship?

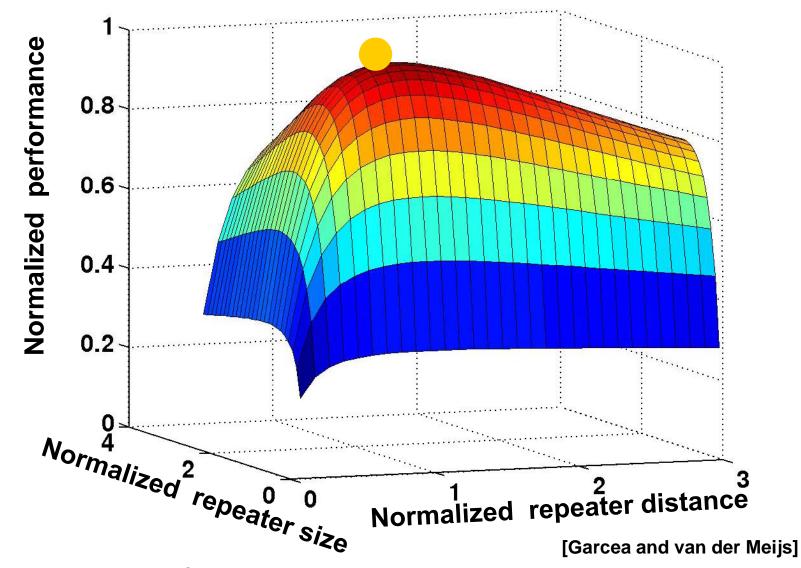
Insert restoring gate at regular intervals!

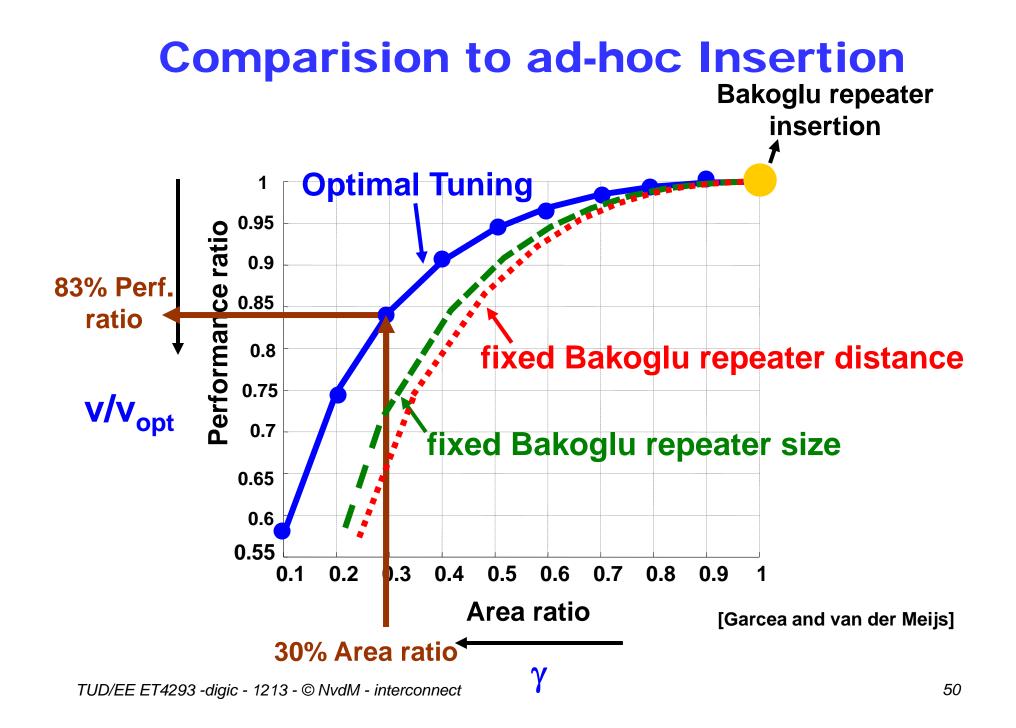


Area Requirements for Optimal Buffering



Performance vs. Repeater Size and Distance





Other Interconnect/Repeater issues

- Optimal repeater sizing for power
- Optimal repeater sizing for minimizing effects of interconnect variability
- Optimize throughput of busses under area and/or power constraints
- Throughput of busses under variability

....

Summary

Capacitance

Area/perimeter model, coupling

Resistance

- **Sheet resistance**
- Interconnect delay

Delay metrics, rc delay, Elmore delay